

N-Channel Super Junction Power MOSFET IV

General Description

The series of devices use advanced trench gate super junction technology and design to provide ultra-low $R_{DS(ON)}$ and low gate charge and With a rapid recovery body diode. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, industrial power applications, Fast charger, new energy vehicle charging pile, on-board OBC etc.

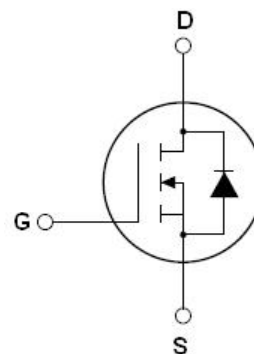
Features

- New technology for high voltage device
- Ultra low on-resistance and ultra low conduction losses
- Ultra Low Gate Charge cause lower driving requirements
- Diode reverse recovery speed is super fast
- High reliability
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies (SMPS)
- Uninterruptible Power Supply (UPS)
- On-board charger (OBC)

$V_{DS \min @ T_{jmax}}$	710	V
$R_{DS(ON)TYP}$	85	mΩ
I_D	36	A
Q_g	55	nC



Schematic diagram

✧ Intrinsic fast-recovery body diode

Package Marking And Ordering Information

Device	Device Package	Marking
NCE65NF099V	DFN8*8	NCE65NF099V

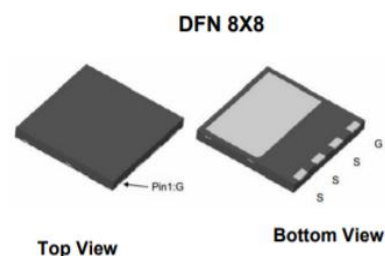


Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	650	V
Gate-Source Voltage ($V_{DS}=0V$) AC ($f>1\text{ Hz}$)	V_{GS}	± 30	V
Gate-Source Voltage ($V_{DS}=0V$) DC	V_{GS}	± 20	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_D (DC)$	36	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_D (DC)$	25.2	A
Pulsed drain current (Note 1)	$I_{DM (pulse)}$	108	A
Maximum Power Dissipation ($T_c=25^\circ\text{C}$)	P_D	346	W
Derate above 25°C		2.30	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note 2)	E_{AS}	324	mJ
Avalanche current (Note 1)	I_{AS}	9	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	3.9	mJ

Parameter	Symbol	Value	Unit
Drain Source voltage slope, $V_{DS} \leq 480V$,	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS} \leq 480V, I_{SD} < I_D$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+175	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	0.43	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =1mA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =650V,V _{GS} =0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =650V,V _{GS} =0V			400	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =500uA	3.5	4.2	5.0	V
Drain-Source On-State Resistance	R _{Ds(ON)}	V _{GS} =10V, I _D =18A		85	99	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz		2800	3200	pF
Output Capacitance	C _{oss}			96		pF
Reverse Transfer Capacitance	C _{rss}			6		pF
Total Gate Charge	Q _g	V _{DS} =480V,I _D =18A, V _{GS} =10V		55	60	nC
Gate-Source Charge	Q _{gs}			16.5		nC
Gate-Drain Charge	Q _{gd}			25.5		nC
Gate plateau voltage	V _{gp}			7.3		V
Intrinsic gate resistance	R _G	f = 1 MHz open drain		1.5		Ω
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =380V,I _D =18A, R _G =1.7Ω,V _{GS} =10V		15		nS
Turn-on Rise Time	t _r			14		nS
Turn-Off Delay Time	t _{d(off)}			72		nS
Turn-Off Fall Time	t _f			14		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _C =25℃			36	A
Pulsed Source-drain current(Body Diode)	I _{SDM}				108	A
Forward On Voltage	V _{SD}	T _J =25℃,I _{SD} =36A,V _{GS} =0V		1.0	1.2	V
Reverse Recovery Time	t _{rr}	T _J =25℃,I _F =18A,di/dt=100A/μs		160		nS
Reverse Recovery Charge	Q _{rr}			0.96		uC
Peak Reverse Recovery Current	I _{rrm}			12		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

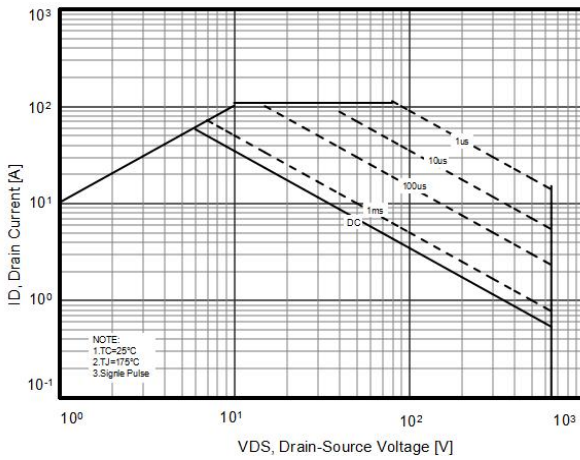


Figure2. Capacitance

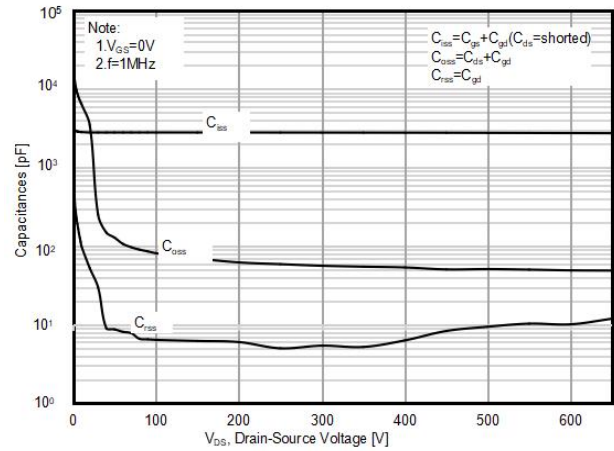


Figure3. Output characteristics

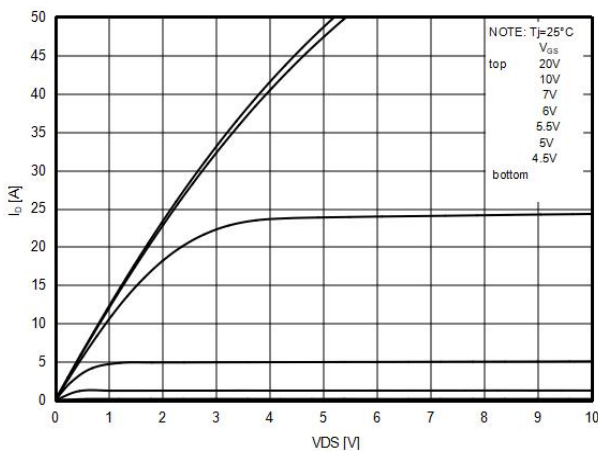


Figure4. Source-Drain Diode Forward Voltage

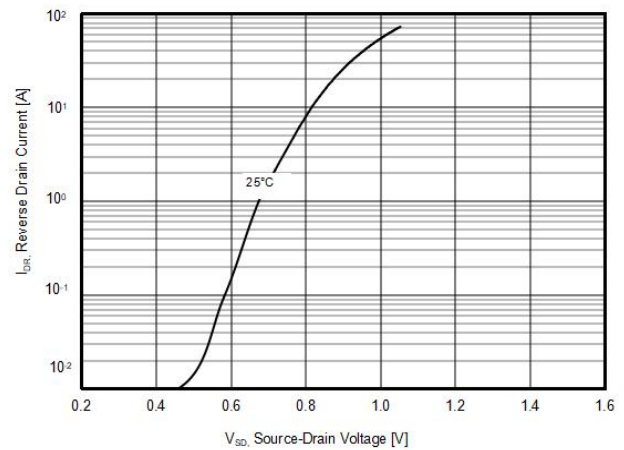


Figure5. Static drain-source on resistance

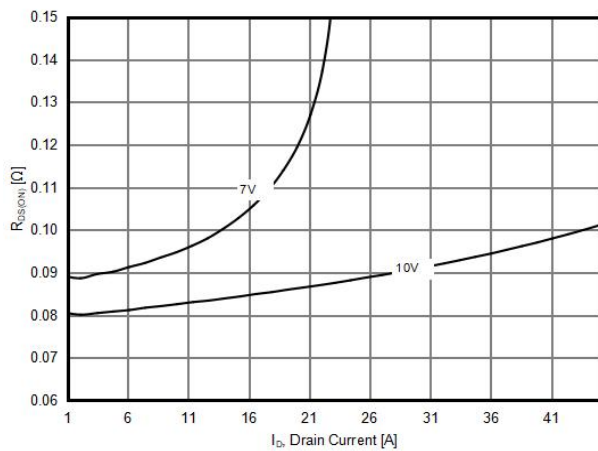


Figure6. Transfer characteristics

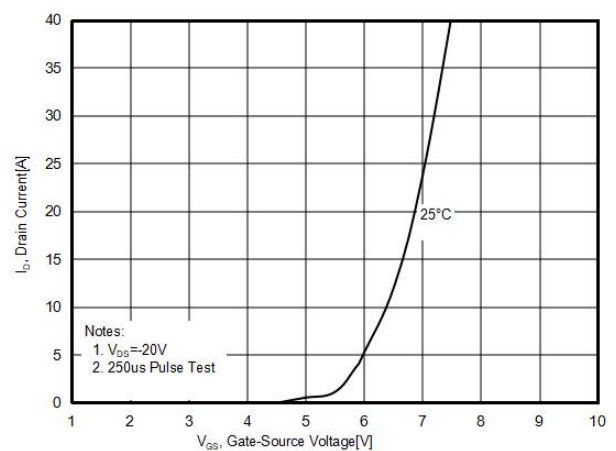


Figure7. $R_{DS(ON)}$ vs Junction Temperature

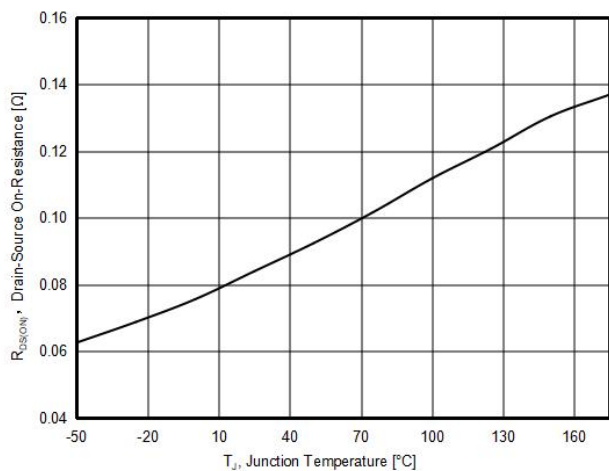


Figure8. BV_{DSS} vs Junction Temperature

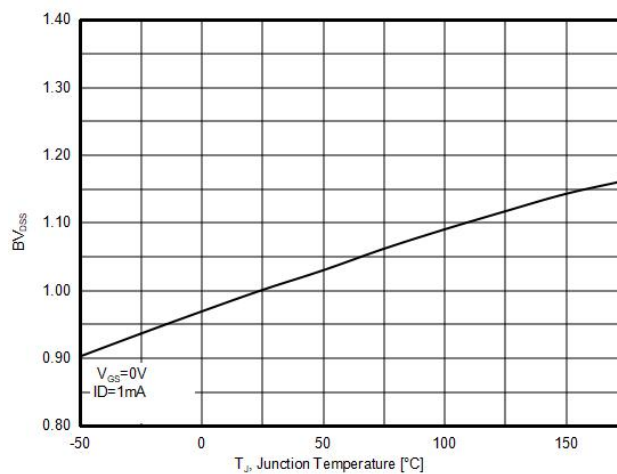


Figure9. Gate charge waveforms

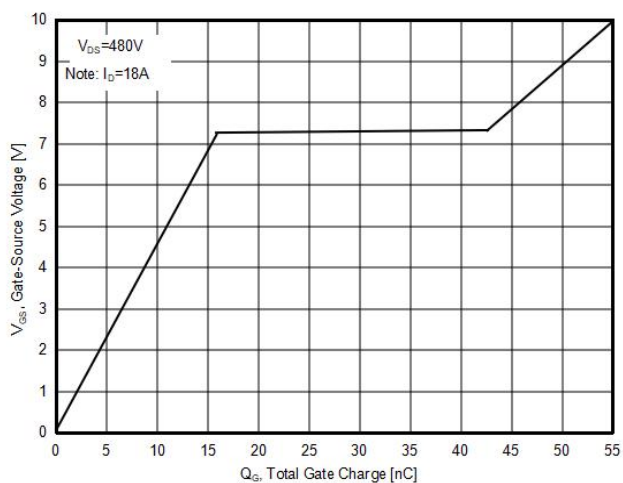
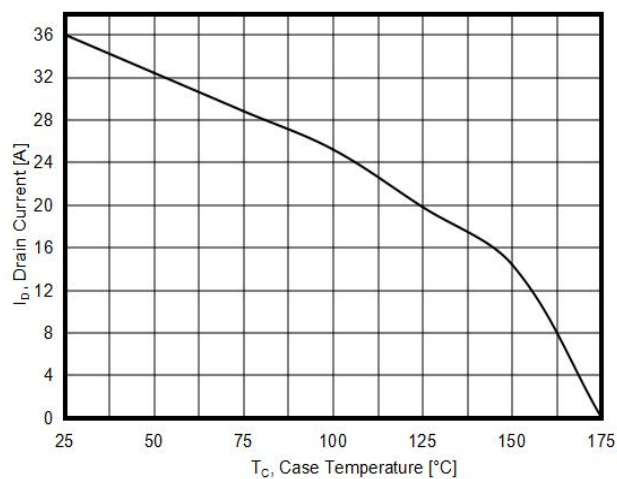
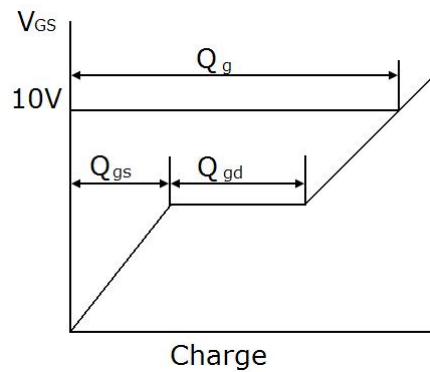
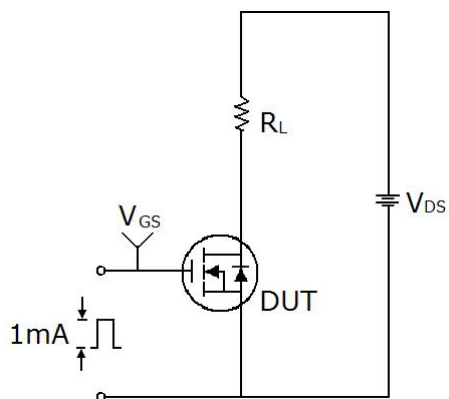


Figure10. Maximum I_D vs Junction Temperature

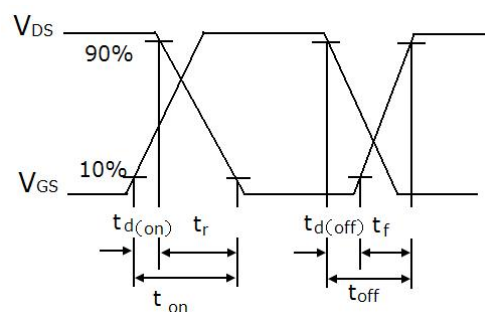
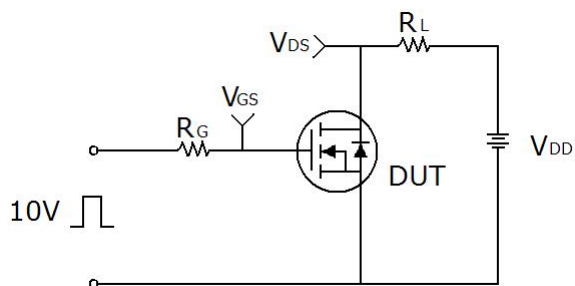


Test circuit

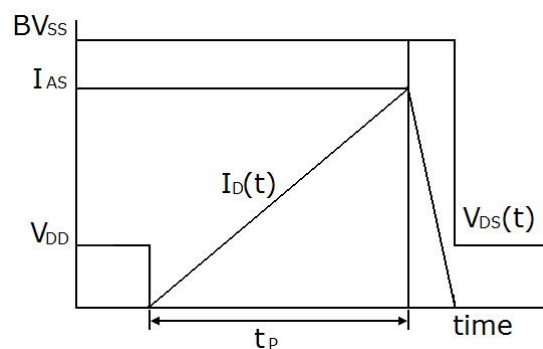
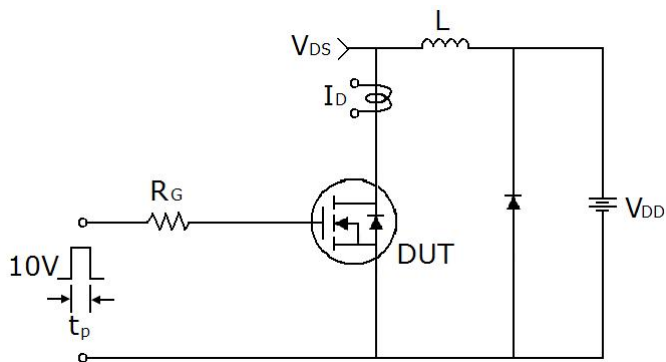
1) Gate charge test circuit & Waveform



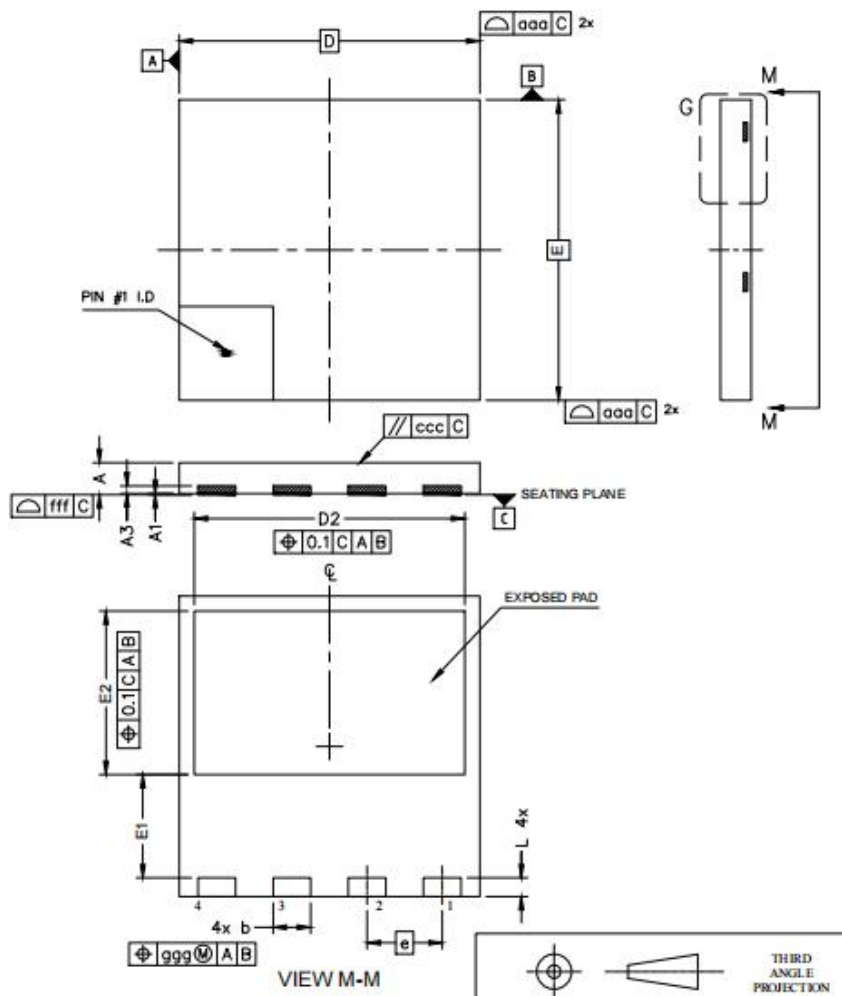
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms



DFN8*8 (B) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.75	0.95	0.030	0.037
A1	0.00	0.05	0.000	0.002
b	0.90	1.10	0.035	0.043
A3	0.10	0.30	0.004	0.012
D	7.90	8.10	0.311	0.319
E	7.90	8.10	0.311	0.319
D2	7.10	7.30	0.280	0.287
E1	2.65	2.85	0.104	0.112
E2	4.25	4.45	0.167	0.175
e	2.00 BSC		0.079 BSC	
L	0.40	0.60	0.016	0.024

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